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PATENT
Nadav H

S/N 097208105

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: SAKAMOTO ET AL. Examiner: O. NADAV
Serial No.: 09/208105 Group Art Unit: 2811
Filed: November 25, 1998 Docket No.: 10233.81USW1
Title: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THEREFOR

CERTIFICATE UNDER 37 CFR 1.6(d):

I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademark Office on November 10, 2002.

By: Lisa Dorn
Name: Lisa Dorn

AMENDMENT UNDER RULE 116

Commissioner for Patents
Washington, D.C. 20231

Dear Commissioner:

In response to the Official Action dated September 6, 2002, please amend this application as follows:

IN THE CLAIMS

Please amend claims 9 and 13-14 to read as follows:

9. (Thrice Amended) A semiconductor device comprising:
~~a substrate having a region irradiated with radiating rays,~~
~~crystal defects within the region irradiated,~~
~~impurity regions formed in the substrate, and~~
~~a metal wiring layer located over the substrate, the metal wiring layer being connected to each of the impurity regions, the metal wiring layer being made of a light metal, the metal wiring layer having an opening above the region irradiated, so that radiating rays passing to the region irradiated through the opening generate the crystal defects only under the opening.~~

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